



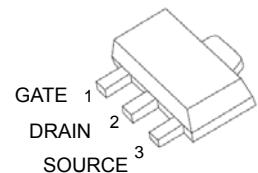
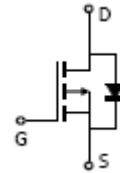
迈拓电子
MAITUO ELECTRONIC

MT9451 P-Channel 20-V(D-S) MOSFET

Description

The Advanced Power MOSFETs provide the designer with the best combination of fast switching, ruggedized device design, ultra low on-resistance and cost-effectiveness.

Marking : A9451



SOT-89-3L

Maximum ratings ($T_a=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Units
Drain-Source Voltage	V_{DS}	-20	V
Continuous Gate-Source Voltage	V_{GS}	± 12	
Continuous Drain Current	I_D	-2.3	A
Power Dissipation	P_D	0.5	W
Thermal Resistance from Junction to Ambient	$R_{\theta JA}$	250	°C/W
Operating Temperature	T_j	150	°C
Storage Temperature	T_{stg}	-55 ~ +150	



迈拓电子
MAITUO ELECTRONIC

Electrical characteristics ($T_a=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Off characteristics						
Drain-source breakdown voltage	$V_{(\text{BR})\text{DSS}}$	$V_{\text{GS}} = 0\text{V}, I_D = 10\mu\text{A}$	-20			V
Gate-body leakage	I_{GSS}	$V_{\text{DS}} = 0\text{V}, V_{\text{GS}} = \pm 12\text{V}$			± 100	nA
Zero gate voltage drain current	I_{DSS}	$V_{\text{DS}} = -20\text{V}, V_{\text{GS}} = 0\text{V}$			-1.0	μA
On characteristics						
Gate-threshold voltage	$V_{\text{GS}(\text{th})}$	$V_{\text{DS}} = V_{\text{GS}}, I_D = -0.25\text{mA}$	-0.50		-1.50	V
Static drain-source on-resistance (note 1)	$R_{\text{DS}(\text{on})}$	$V_{\text{GS}} = -4.5\text{V}, I_D = -2.3\text{A}$			0.130	Ω
		$V_{\text{GS}} = -2.5\text{V}, I_D = -1.0\text{A}$			0.220	
Forward transconductance (note 1)	g_{fs}	$V_{\text{DS}} = -5\text{V}, I_D = -2.3\text{A}$	2.3			S
Dynamic characteristics (note 2)						
Input capacitance	C_{iss}	$V_{\text{DS}} = -20\text{V}, V_{\text{GS}} = 0\text{V}, f = 1\text{MHz}$			430	pF
Output capacitance	C_{oss}				100	
Reverse transfer capacitance	C_{rss}				35	
Switching characteristics						
Turn-on delay time (note 1,2)	$t_{\text{d}(\text{on})}$	$V_{\text{GS}} = -5\text{V}, V_{\text{DS}} = -10\text{V}, I_D = -1\text{A}, R_G = 3.3\Omega, R_D = 10\Omega$			9	ns
Rise time (note 2)	t_r				25	
Turn-off delay time (note 2)	$t_{\text{d}(\text{off})}$				20	
Fall time (note 2)	t_f				10	
Drain-source body diode characteristics						
Body diode forward voltage (note 1)	V_{SD}	$I_S = -1\text{A}, V_{\text{GS}} = 0\text{V}$			-1.6	V

No tes:

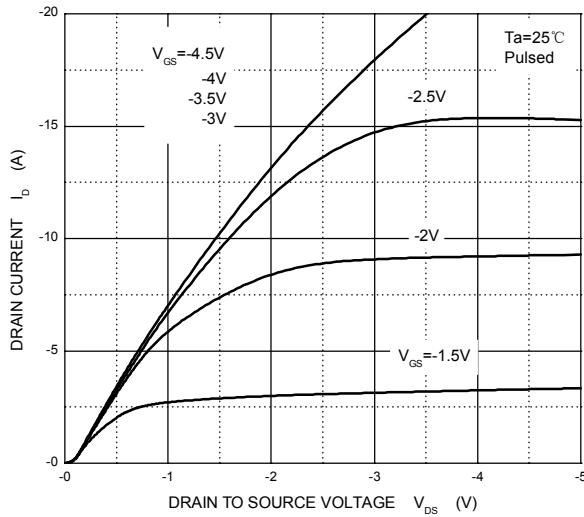
1. Pulse Test ; Pulse Width $\leq 300\mu\text{s}$, Duty Cycle $\leq 2\%$.
2. These parameters have no way to verify.



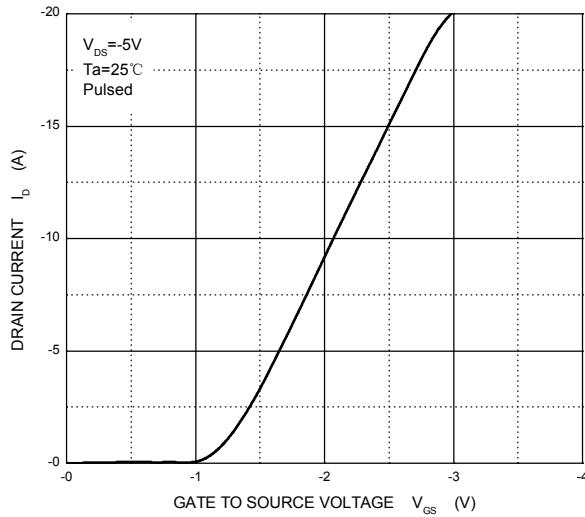
迈拓电子
MAITUO ELECTRONIC

Typical Characteristics

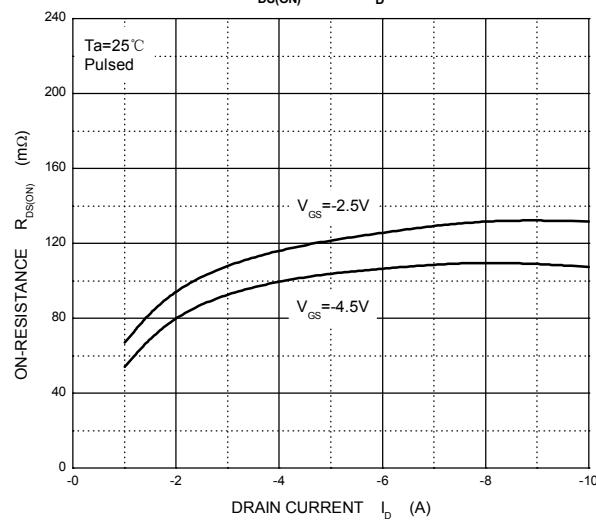
Output Characteristics



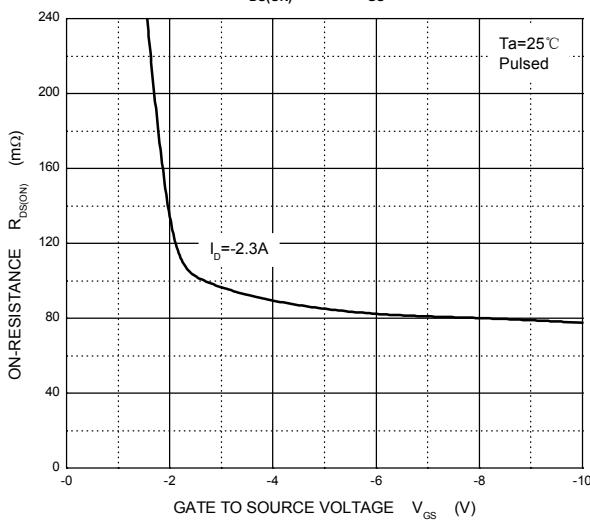
Transfer Characteristics



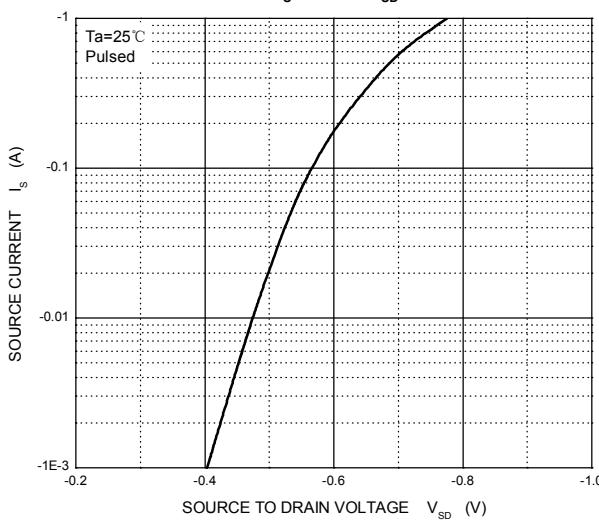
$R_{DS(ON)}$ — I_D



$R_{DS(ON)}$ — V_{GS}



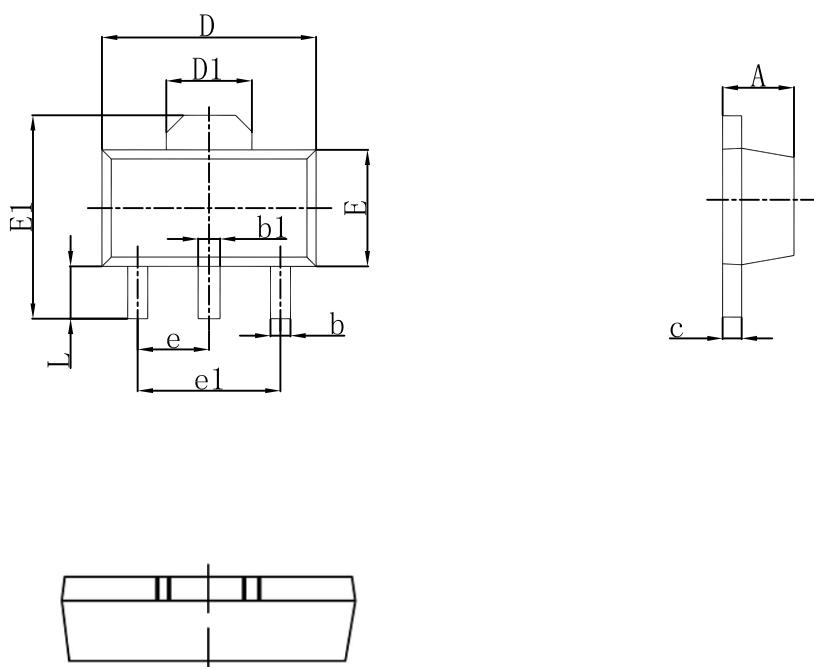
I_S — V_{SD}





迈拓电子
MAITUO ELECTRONIC

SOT-89-3L Outlines Dimensions



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	1.400	1.600	0.055	0.063
b	0.320	0.520	0.013	0.020
b1	0.400	0.580	0.016	0.023
c	0.350	0.440	0.014	0.017
D	4.400	4.600	0.173	0.181
D1	1.550 REF.		0.061 REF.	
E	2.300	2.600	0.091	0.102
E1	3.940	4.250	0.155	0.167
e	1.500 TYP.		0.060 TYP.	
e1	3.000 TYP.		0.118 TYP.	
L	0.900	1.200	0.035	0.047